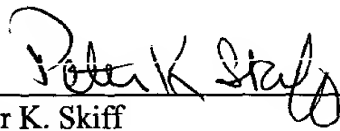


REMARKS

The present application has been amended to correct a typographical error in a patent number cited. In view of the foregoing, favorable action in connection with this application is respectfully requested.

Respectfully submitted,

BURNS, DOANE, SWECKER & MATHIS, L.L.P.

By: 
Peter K. Skiff
Registration No. 31,917

P.O. Box 1404
Alexandria, Virginia 22313-1404
(703) 836-6620

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Attorney's Docket No. 015290-502

Application No. 09/820,694

Page 1

Attachment to Preliminary Amendment dated July 12, 2001

Marked-up Copy

Page 8, first full paragraph beginning at line 8

The plasma for carrying out the silicon nitride etch can be produced in various types of plasma reactors. Such plasma reactors typically have energy sources which use RF energy, microwave energy, magnetic fields, etc. to produce a medium to high density plasma. For instance, a high density plasma could be produced in a transformer coupled plasma (TCP™) available from Lam Research Corporation which is also called inductively coupled plasma reactor, an electron-cyclotron resonance (ECR) plasma reactor, a helicon plasma reactor, or the like. An example of a high flow plasma reactor which can provide a high density plasma is disclosed in commonly owned U.S. Patent No. [5,820,261] 5,820,723, the disclosure of which is hereby incorporated by reference. The plasma can also be produced in a parallel plate etch reactor such as the dual frequency plasma etch reactor described in commonly owned U.S. Patent No. 6,090,304, the disclosure of which is hereby incorporated by reference.